Structure and Properties of Titanium Oxide Layers prepared by Metal Plasma Immersion Ion Implantation and Deposition



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For medical materials in contact with blood it is important to minimize the tendency of their surface to adsorb blood proteins and to induce blood clotting, hence, to reduce the danger of thrombosis. Coatings based on titanium oxide are a very promising approach in this direction

Objectives

Synthesis of bioinert and blood compatible coatings based on titanium oxide by Metal Plasma Immersion Ion Implantation and Deposition (MePIIID), modification of the surface layers by ion implantation (P and Cr) and annealing

Study of the dependence of crystal structure (crystalline rutile, anatase and brookite, nanocrystalline, amorphous TiO₂), surface roughn s and electrical properties of titanium oxide layers on the deposition parameters

Investigation of the relation between physical properties of the titanium oxide layers and blood compatibility

Summary

- MePIIID provides a useful technique to control composition and structure of titanium oxide films. In dependence on the deposition parameters amorphous and nanocrystalline structures, crystalline layers composed of anatase and brookite as well as layers dominated by the rutile phase have been produced
- Crystal structure and crystallite size of titanium oxide films seem to have only minimal influence on the activation of the plasmatic clotting system. As a trend, amorphous , nanocrystalline and fine-grained layers induce less clotting of blood plasma than well crystallized rutile films
- P and Cr implantation clearly reduces the clot forming property of the surface
- Microstructure of the Ti oxides showed a opposite effects on platelet adherence and activation of the clotting cascade. However, P*- doped rutile shows an improved behaviour in both cases
- · Roughness of the surface below 50 nm seems to be no important parameter

Experimental

Deposition parameters:

Specimen temperature (Tmax):
Oxygen flow rate (F):
Bias voltage (ion energy):
TiO ₂ deposition rate (R _{dep}):
Current of the cathodic
arc discharge (I):
Basic vacuum:
Working pressure:
Substrate:

Implantation:

Post-implantation ing: AES Analysis RBS: AFM

Blood compatibility

only weal 100

80

60

40

0

100

80 60

40

20

0 0

(at.%) 20

Concentration

for U=2.5 kV and F=180 sccm

depth distribution of the elements phase formation and identification thickness of the deposited films s of the deposited films sheet resistance Four point probe technique

900 °C for 1 h (vacuum)

25 - 500 °C 60 - 180 sccm

0 – 2.5 kV

110 A

 $0.2 - 1.1 \,\mu$ m/min

0.5 – 1 x 10⁻³ Pa 0.5 – 1 x 10⁻¹ Pa

SiO₂ on Si (100)

1015 P+/cm2 (30 keV);

5x10¹⁷ Cr⁺/cm² (30 keV)

blood clotting time platelet adhesion and activation

Oxygen concentration and deposition rate

(see Fig. 1), substrate temperature and implantation voltage, TiO₂ is formed

deposition rate increases strongly with substrate temperature 450 $^{\circ}C$ - 1.1 $\mu m/$ 60 s and ~ 116 $^{\circ}C$ - 0.23 $\mu m/$ 60 s

influence of the implantation voltage on the deposition rate is

----0

400

200

250

Si

500

increasing F reduces the deposition rate strongly

60 sccm - 540 nm/ 60 s, 120 sccm- 350 nm/ 60 s, 180 sccm- 240 nm/60 s

200 100

b F = 180 sccm O

300

for U=2.5 kV and Tmax~120°C (see Fig.1)

a $F = 60 \text{ sccm } O_2$

oxygen concentration is nearly independent of oxygen flow rate F

U ŧ

MePIIID:metal deposition + plasma immersion ion implantation (PIII)

metal plasma by cathodic arc evaporation implantation by pulsed negative substrate bias

supply of oxygen near the substrate

Schematic diagram of the MePIIID device

Layer properties

Phase composition of the oxide layer Dependence of the Ti oxide structure on the deposition parameters

structure	T. ºC	F, sccm	U. kV	
rutile	~ 450	180	- 2.5	
anatase + brookite	~ 350	60	- 2.5	
amorphous TiO ₂ - layer	~ 80	180	0	
nanocrystalline anatase + brookite	~ 60	60	0	
Electrical properties and roughnes	s of the	different T	i oxide la	avei

structure	sheet resistance	roughness S., nm
rutile	>200 kOhm	high – 34.2
rutile + P* implantation (II)	~90 kOhm	high – 30.1
rutile + P*-II + annealing	~60 kOhm	high – 39.8
anatase + brookite	~25 Ohm	high – 42.7
amorphous TiO2- layer	>200 kOhm	low – 4.15
amorphous TiO2- layer + Cr+-II	~100 Ohm	high – 31.9
nanocrystalline anatase + brookite	~100 Ohm	low – 5.35

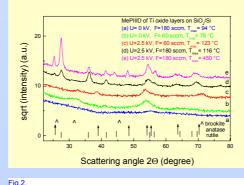


Fig.2. XRD pattern of Ti oxide layers deposited with different parameters

Blood compatibility

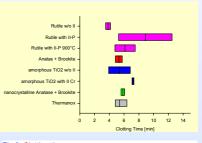


Fig.3. Clotting time Median and quartils of the blood clotting time on the test surfaces

- both P* and Cr* ion implantation (II-P and II-Cr) increase the clotting time, i.e. reduce the activation of the clotting cascade by this surface
- well crystallized samples dominated by the rutile structure show the lowest clotting time
- the behaviour of the amorphous and nanocrystalline samples is in between

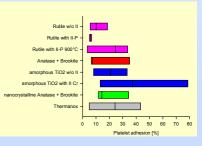


Fig.4. Platelet adhesion:

Bars indicate median and quartils of the percent adherent platelets from a sample platelet rich plasma on the test surfaces

- P⁺ ion implantation (II-P) reduces the platelet adherence to the surface, whereas Cr⁺ ion implantation (II-Cr) greatly increases it
- As a vague trend lower platelet adherence on crystalline coatings than on amorphous ones is found (contrary to the behaviour of the clotting time)

Fig.1. AES depth profiles of Ti oxide layers deposited with U = 2.5 kV at Tmax = 120 °C for different oxygen flow rates F

100

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50

150

Depth (nm)

